# **OSRAM** CT ELLN51.14 **Datasheet**







# Chip LED

# **CT ELLN51.14**

With enhanced brightness, the CT ELLN51.14 ensures more precise heart rate measurements. Its ultra-compact design is perfect for space-constrained wearables such as rings and inear headphones.

Additionally, its increased efficiency extends battery life at system level.







## **Applications**

- Digital Diagnostic Devices

- Vital Sign Monitoring

#### **Features**

- Package: clear silicone
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)
- SMT package
- Suitable for SMT assembly
- Available on tape and reel



**Ordering Information** 

Туре Ordering Code Total radiant flux 1)

typ.

 $I_{\rm F}$  = 20 mA;  $t_{\rm p}$  = 20 ms

CT ELLN51.14 14 mW Q65113A7798



# **Maximum Ratings**

 $T_{_{\rm S}}$  = 25 °C

Parameter	Symbol		Values
Operating temperature	T <sub>op</sub>	min.	-40 °C
		max.	85 °C
Storage temperature	T <sub>stg</sub>	min.	-40 °C
	o.g	max.	85 °C
Junction temperature	T <sub>j</sub>	max.	100 °C
Forward current	I <sub>F</sub>	max.	30 mA
Forward current pulsed	   F pulse	max.	0.75 A
$t_{p} \le 50 \ \mu s; \ D \le 0.005$	. paice		
Reverse voltage <sup>2)</sup>	$V_R$	max.	5 V
Power consumption	P <sub>tot</sub>	max.	90 mW
ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)	$V_{ESD}$	max.	2 kV



## **Characteristics**

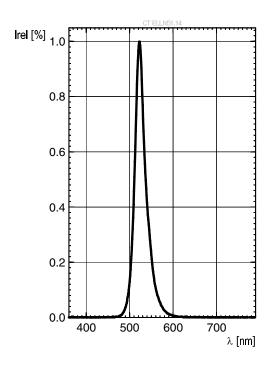
 $I_{_{\rm F}}$  = 20 mA;  $t_{_{
m D}}$  = 20 ms;  $T_{_{
m S}}$  = 25 °C

Parameter	Symbol	Values	
Peak wavelength	$\lambda_{peak}$	typ.	526 nm
Centroid wavelength 3)	$\lambda_{centroid}$	min.	522 nm
		typ.	530 nm
		max.	541 nm
Spectral bandwidth at 50% I <sub>rel,max</sub> (FWHM)	Δλ	typ.	26 nm
Half angle	φ	typ.	60 °
Dimensions of active chip area	LxW	typ.	0.5 x 0.5 mm x mm
Rise time (10% / 90%) $I_F = 100 \text{ mA}; R_L = 50 \Omega$	t,	typ.	59 ns
Fall time (10% / 90%) $I_F = 100 \text{ mA}; R_L = 50 \Omega$	t <sub>f</sub>	typ.	59 ns
Forward voltage 4)	$V_{_{\rm F}}$	min.	2.20 V
	,	typ.	2.40 V
		max.	2.80 V
Reverse current 2)	I <sub>R</sub>	typ.	0.01 μΑ
$V_R = 5 V$	ĸ	max.	10 μA
Total radiant flux 1)5)	Фе	min.	11 mW
$I_{\rm F} = 20 \text{ mA}; t_{\rm D} = 20 \text{ ms}$	Ç	typ.	14 mW
		max.	17.25 mW
Thermal resistance junction solder point real <sup>6)</sup>	$R_{thJSreal}$	typ.	110 K / W
		max.	140 K / W



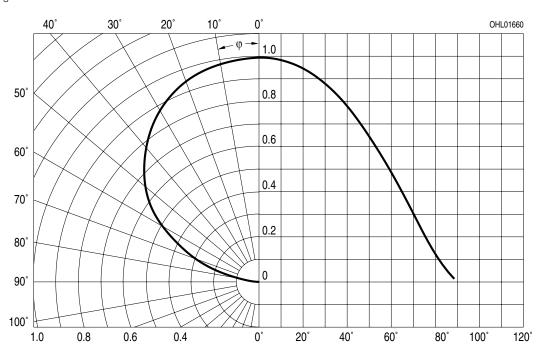
# Relative Spectral Emission 7), 8)

 $I_{e,rel}$  = f ( $\lambda$ );  $I_{F}$  = 20 mA;  $t_{p}$  = 20 ms



### Radiation Characteristics 7), 8)

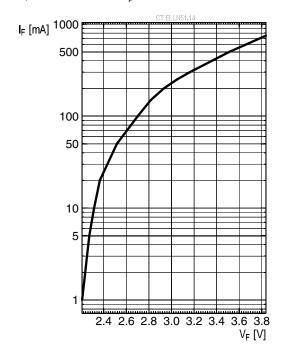
 $I_{rel} = f(\phi); T_S = 25 °C$ 



# **OSRAM**

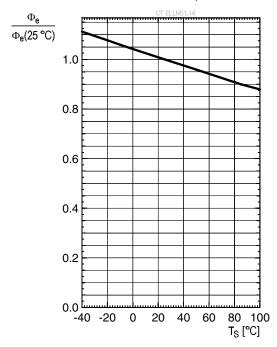
# Forward current 7), 8)

 $I_F = f(V_F)$ ; single pulse;  $t_D = 100 \mu s$ 



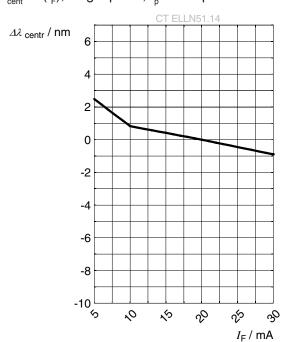
#### Relative Total Radiant Flux 7), 8)

 $\Phi_{\rm e}/\Phi_{\rm e}(20{\rm mA})$  = f (I<sub>F</sub>); single pulse; t<sub>p</sub> = 100  $\mu {\rm s}$ 



## Relative Centroid Wavelength 7), 8)

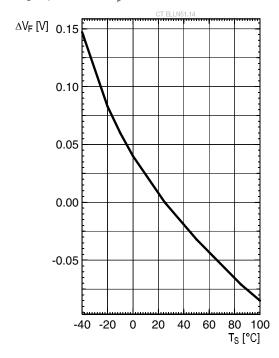
 $\Delta \lambda_{cent} = f(I_F)$ ; single pulse;  $t_D = 100 \mu s$ 





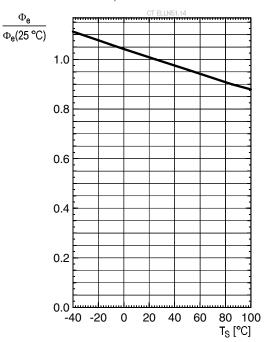
### Relative Forward Voltage 7)

$$V_F = f(T_S); I_F = 20mA; t_p = 100\mu s$$



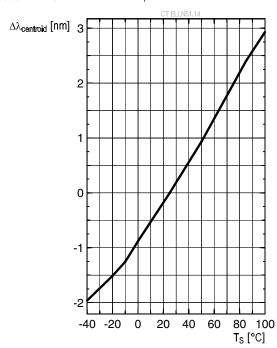
#### Relative Total Radiant Flux 7)

$$\Phi_{rel} = f(T_S); I_F = 20mA; t_p = 100\mu s$$



## Relative Centroid Wavelength 7)

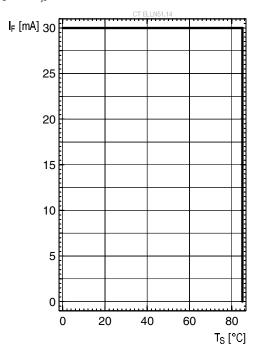
$$\lambda_{centroid}$$
 = f(T<sub>S</sub>); I<sub>F</sub> = 20mA; t<sub>p</sub> = 20ms





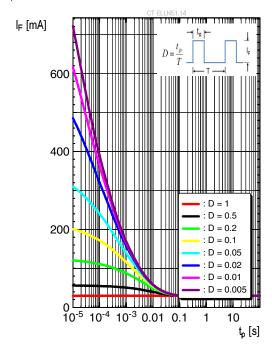
#### Max. Permissible Forward Current

$$I_F = f(T_S)$$
; Rth<sub>js</sub> = 140 K / W



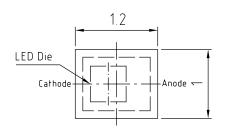
## **Permissible Pulse Handling Capability**

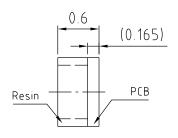
 $I_F = f(t_p)$ ; duty cycle D = parameter;  $T_S = 85$ °C

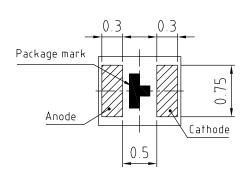




# Dimensional Drawing 9)







general tolerance ±0.1

lead finish Au

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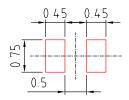
### **Further Information:**

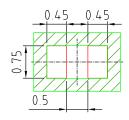
**Approximate Weight:** 1.2 mg

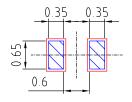
Pin	Description	
1	Cathode	
2	Anode	



#### Recommended Solder Pad 9)





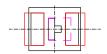






solder stencil recomended stencil thickness 120µm, type 4 solder paste

### Component Location on Pad

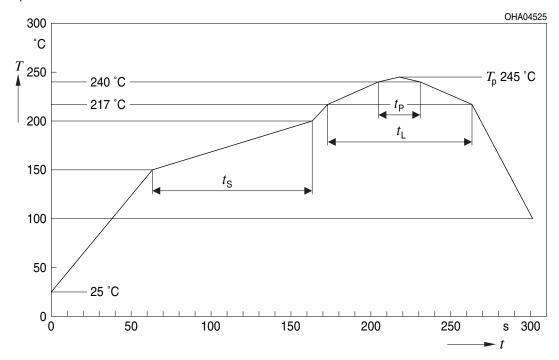


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## **Reflow Soldering Profile**

Product complies to MSL Level 3 acc. to JEDEC J-STD-020E



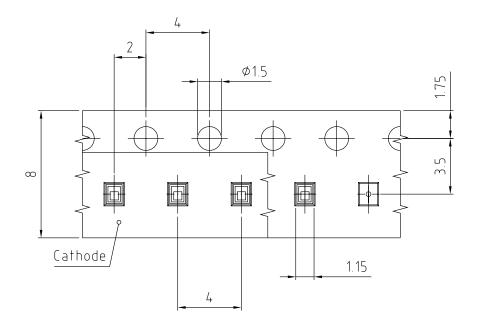
Profile Feature	Symbol	Pb	-Free (SnAgCu) Ass	Unit	
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat*)	'		2	3	K/s
25 °C to 150 °C					
Time t <sub>s</sub>	t <sub>s</sub>	60	100	120	S
$T_{Smin}$ to $T_{Smax}$					
Ramp-up rate to peak*)			2	3	K/s
$T_{Smax}$ to $T_{P}$					
Liquidus temperature	$T_{L}$		217		°C
Time above liquidus temperature	$t_{\scriptscriptstyle \perp}$		80	100	S
Peak temperature	T <sub>P</sub>		245	260	°C
Time within 5 °C of the specified peak	t <sub>P</sub>	10	20	30	S
temperature T <sub>P</sub> - 5 K					
Ramp-down rate*			3	6	K/s
T <sub>P</sub> to 100 °C					
Time				480	S
25 °C to T <sub>P</sub>					

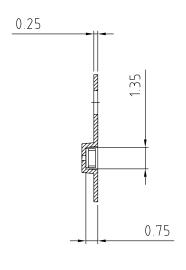
All temperatures refer to the center of the package, measured on the top of the component

<sup>\*</sup> slope calculation DT/Dt: Dt max. 5 s; fulfillment for the whole T-range



# Taping 9)

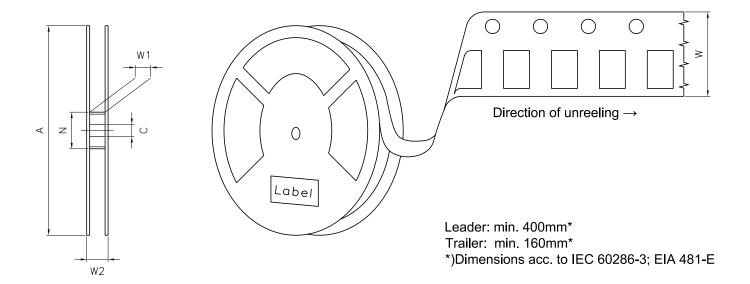




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## Tape and Reel 10)



#### **Reel Dimensions**

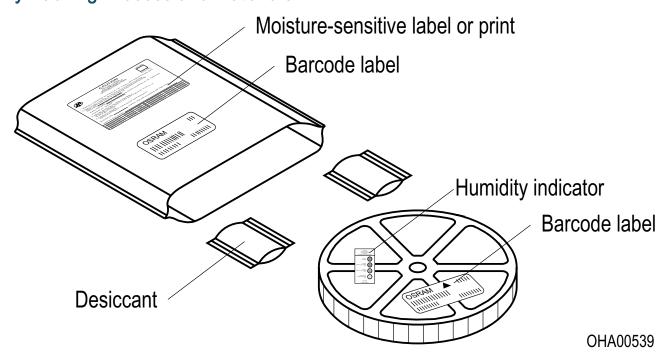
Α	W	$N_{\min}$	$W_1$	$W_{2 max}$	Pieces per PU
180 mm	8 + 0.3 / - 0.1 mm	60 mm	8.4 + 2 mm	14.4 mm	4000



#### **Barcode-Product-Label (BPL)**



## Dry Packing Process and Materials 9)



Moisture-sensitive product is packed in a dry bag containing desiccant and a humidity card according JEDEC-STD-033.



#### **Notes**

The evaluation of eye safety occurs according to the standard IEC 62471:2006 (photo biological safety of lamps and lamp systems). Within the risk grouping system of this IEC standard, the device specified in this data sheet falls into exempt risk group - Exempt.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit https://ams-osram.com/support/application-notes



#### Disclaimer

#### Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on our website.

#### **Packing**

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

#### Product and functional safety devices/applications or medical devices/applications

Our components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

Our products are not qualified at module and system level for such application.

In case buyer – or customer supplied by buyer – considers using our components in product safety devices/ applications or medical devices/applications, buyer and/or customer has to inform our local sales partner immediately and we and buyer and /or customer will analyze and coordinate the customer-specific request between us and buyer and/or customer.



#### Glossary

- Total radiant flux: Measured with integrating sphere.
- 2) Reverse Operation: This product is intended to be operated applying a forward current within the specified range. Applying any continuous reverse bias or forward bias below the voltage range of light emission shall be avoided because it may cause migration which can change the electro-optical characteristics or damage the LED.
- 3) **Wavelength:** The wavelengths are measured with a tolerance of ±1 nm.
- 4) Forward Voltage: The forward voltages are measured with a tolerance of ±0.1 V.
- 5) **Brightness:** The brightness values are measured with a tolerance of ±11%.
- 6) Thermal resistance: junction - soldering point, of the device only, mounted on an ideal heatsink (e.g. metal block)
- 7) Typical Values: Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 8) **Testing temperature:** TA = 25°C (unless otherwise specified)
- 9) Tolerance of Measure: Unless otherwise noted in drawing, tolerances are specified with ±0.1 and dimensions are specified in mm.
- Tape and Reel: All dimensions and tolerances are specified acc. IEC 60286-3 and specified in mm.



# **Revision History**

Version	Date	Change
1.0	2025-03-24	Initial Version
1.1	2025-04-15	Characteristics Electro - Optical Characteristics (Diagrams)
1.2	2025-06-10	Description



EU RoHS and China RoHS compliant product 此产品符合欧盟 RoHS 指令的要求; 按照中国的相关法规和标准, 不含有毒有害物质或元素。

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